Philips Semiconductors

Product specification

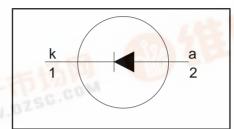
Rectifier diodes Schottky barrier

PBYR745F, PBYR745X series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Isolated mounting tab

SYMBOL



QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{F(AV)} = 7.5 \text{ A}$
 $V_F \le 0.57 \text{ V}$

GENERAL DESCRIPTION

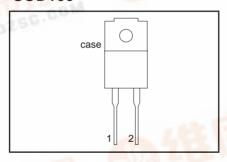
Schottky rectifier diodes in a plastic envelope with electrically isolated mounting tab. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR745F series is supplied in the SOD100 package. The PBYR745X series is supplied in the SOD113 package.

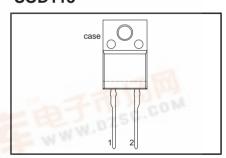
PINNING

PIN	DESCRIPTION	
1	cathode	
2	anode	
tab	isolated	

SOD100



SOD113



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	M	AX.	UNIT
V _{RRM}	Peak repetitive reverse	PBYR7 PBYR7	-	40F 40X 40	45F 45X 45	V
V_{RWM}	voltage Working peak reverse voltage		="	40	45	V
V_R	Continuous reverse voltage	T _{hs} ≤ 103 °C	4.	40	45	V
I _{F(AV)}	Average rectified forward current	square wave; $\delta = 0.5$; $T_{hs} \le 123$ °C	-	7.5		А
I _{FRM}	Repetitive peak forward current	square wave; $\delta = 0.5$; $T_{hs} \le 123$ °C	-	15		Α
I _{FSM}	Non-repetitive peak forward current	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	-		00 10	A A
I _{RRM}	Peak repetitive reverse surge current	pulse width and repetition rate limited by T _{i max}	-		1	А
T _j	Operating junction temperature	Jillax	-	1	50	°C
T _{stg}	Storage temperature		- 65	1	75	°C

PBYR745F, PBYR745X series

ISOLATION LIMITING VALUE & CHARACTERISTIC

T_{hs} = 25 °C unless otherwise specified

ns — Camero Charles						
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Peak isolation voltage from both terminals to external heatsink	SOD100 package; R.H. ≤ 65%; clean and dustfree	1	1	1500	>
V _{isol}	R.M.S. isolation voltage from both terminals to external heatsink	SOD113 package; f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	1	-	2500	٧
C _{isol}	Capacitance from pin 1 to external heatsink	f = 1 MHz	1	10	-	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Thermal resistance junction to heatsink	with heatsink compound	-	-	5.5	K/W
R _{th j-a}	100 110 0110 1111	in free air	-	55	-	K/W

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_F = 7.5 \text{ A}; T_j = 125^{\circ}\text{C}$ $I_F = 15 \text{ A}; T_j = 125^{\circ}\text{C}$	-	0.45	0.57	٧
		$I_{\rm F} = 15 \text{A}; T_{\rm i} = 125 ^{\circ} \text{C}$	-	0.65	0.72	V
		$I_{\rm F} = 15 \text{A}$	-	0.64	0.84	V
I _R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	0.13	1	mA
		$V_R = V_{RWM}$; $T_i = 100$ °C	-	17	22	mA
C _d	Junction capacitance	$V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_j = 25 ^{\circ}\text{C}$ to $125 ^{\circ}\text{C}$	-	270	-	pF

PBYR745F, PBYR745X series

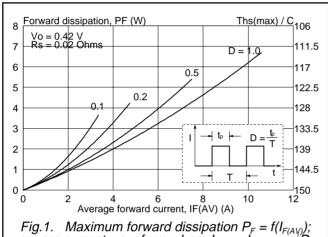


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)});$ square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}.$

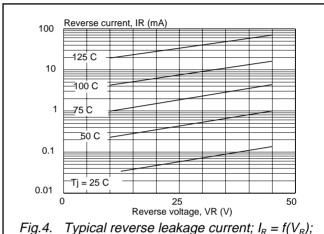


Fig.4. Typical reverse leakage current; $I_R = f(V_R)$; parameter T_i

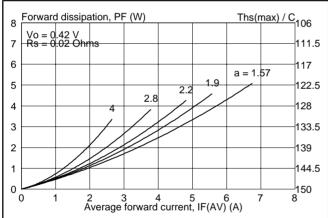
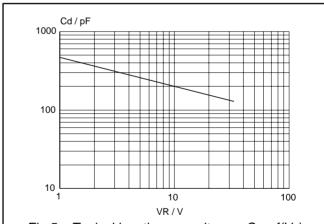


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)});$ sinusoidal current waveform where a = f(AV) $factor = I_{F(RMS)} / I_{F(AV)}$.



Typical junction capacitance; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25 ^{\circ}\text{C}$ to $125 ^{\circ}\text{C}$. Fig.5.

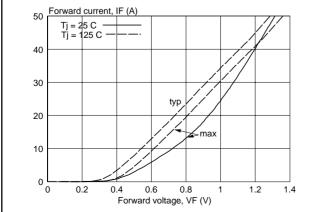


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

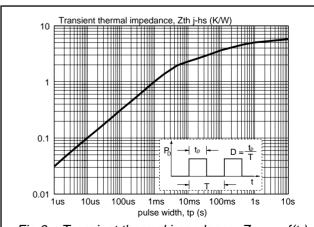
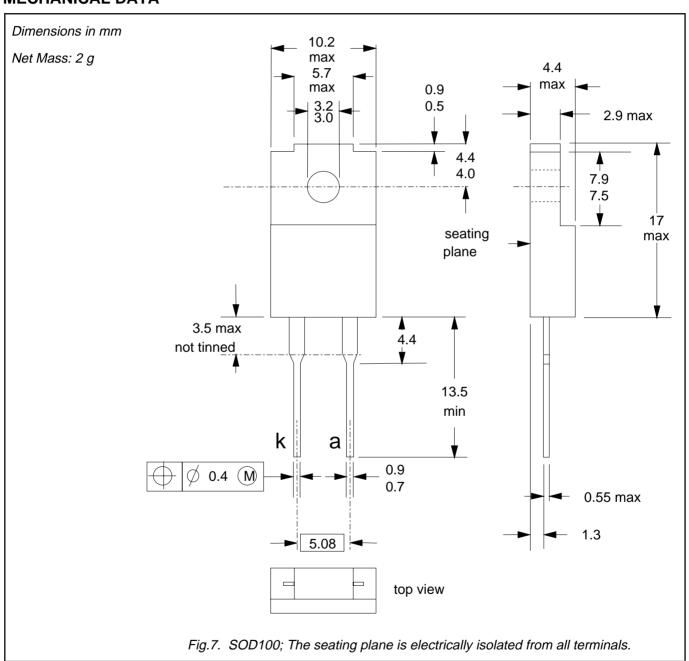


Fig.6. Transient thermal impedance; $Z_{th j-hs} = f(t_p)$.

PBYR745F, PBYR745X series

MECHANICAL DATA

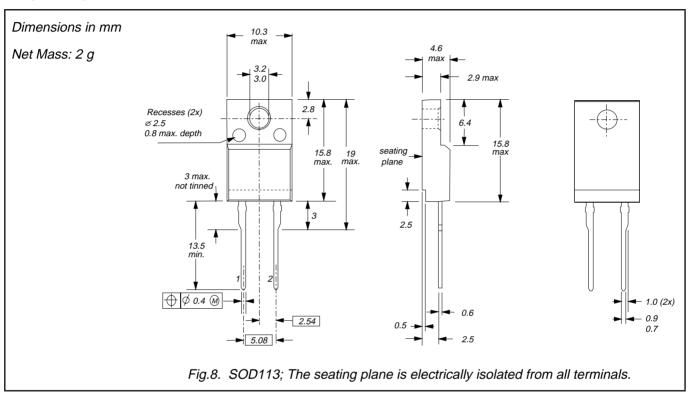


Notes

- Refer to mounting instructions for F-pack envelopes.
 Epoxy meets UL94 V0 at 1/8".

PBYR745F, PBYR745X series

MECHANICAL DATA



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 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

PBYR745F, PBYR745X series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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